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Vishay/Siliconix SUP60N06-12P-E3

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SUP60N06-12P

Vishay Siliconix

RoHS

COMPLIANT

HALOGEN

FREE Available

N-Channel 60-V (D-S) MOSFET

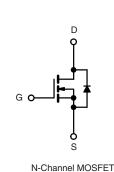
PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)		
60	0.012 at V_{GS} = 10 V	60 ^d	33		

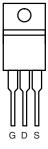
FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- 100 % Rg Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Synchronous Rectifier
- Power Supplies





TO-220AB

Top View

Ordering Information: SUP60N06-12P-E3 (Lead (Pb)-free) SUP60N06-12P-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	$T_{\rm C}$ = 25 °C, unless oth	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	60	v		
Gate-Source Voltage		V _{GS}	± 20	v	
Continuous Drain Current ($T_1 = 150 \ ^{\circ}C$)	T _C = 25 °C		60 ^d		
Continuous Drain Current $(1) = 150^{\circ}$ C)	T _C = 70 °C	I _D	54 ^d	A	
Pulsed Drain Current		I _{DM}	80		
Avalanche Current		I _{AS}	40		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	80	mJ	
	T _C = 25 °C	р	100 ^b	14/	
Maximum Power Dissipation ^a	T _A = 25 °C ^c	– P _D –	3.25	W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	1.25	0/11	

Notes:

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When Mounted on 1" square PCB (FR-4 material).

d. Package limited.



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SPECIFICATIONS $T_J = 25^{\circ}$	C, unless of	therwise noted				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 V, I_D = 250 \mu A$	60			v
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	2.5		4.5	v
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA
Zero Gate Voltage Drain Current		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
	I _{DSS}	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$			50	
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 150 ^{\circ}\text{C}$			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	80			Α
Drain-Source On-State Resistance ^a		V _{GS} = 10 V, I _D = 30 A		0.0098	0.012	Ω
	R _{DS(on)}	V_{GS} = 10 V, I _D = 30 A, T _J = 125 °C		0.0155	0.019	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		37		S
Dynamic ^b	•		•			
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz		1970		pF
Output Capacitance	C _{oss}			310		
Reverse Transfer Capacitance	C _{rss}			110		
Total Gate Charge ^c	Qg			33	55	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30$ V, $V_{GS} = 10$ V, $I_{D} = 20$ A		11		
Gate-Drain Charge ^c	Q _{gd}			9		
Gate Resistance	Rg	f = 1 MHz	0.3	1.4	2.8	Ω
Turn-On Delay Time ^c	t _{d(on)}			11	20	
Rise Time ^c	tr	V_{DD} = 30 V, $\rm R_{L}$ = 1.53 Ω $\rm I_{D}$ \cong 20 A, $\rm V_{GEN}$ = 10 V, $\rm R_{g}$ = 1 Ω		11	20	ns
Turn-Off Delay Time ^c	t _{d(off)}			16	30	
Fall Time ^c	t _f			8	15	
Source-Drain Diode Ratings and Ch	aracteristics 7	_C = 25 °C ^b				
Continuous Current	۱ _S				60	
Pulsed Current	I _{SM}		1		80	A
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V		0.84	1.5	V
Reverse Recovery Time	t _{rr}		1	40	80	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 10 A, dl/dt = 100 A/μs		3.2	5.0	A
Reverse Recovery Charge	Q _{rr}			64	120	nC

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





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= - 55 °C

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T_J = 125 °C

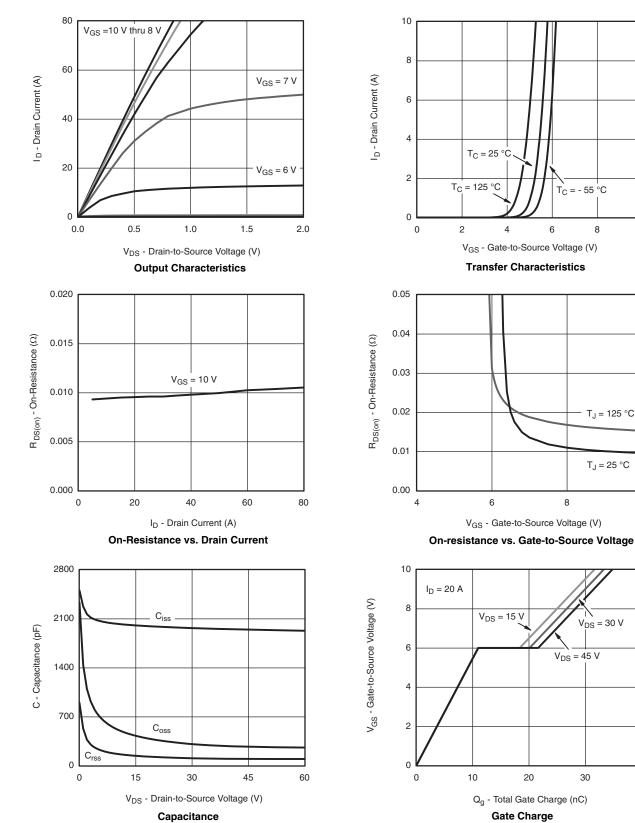
T_J = 25 °C

V_{DS} = 30 V

30

10

10



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Document Number: 69070 S10-1475-Rev. C, 05-Jul-10 40

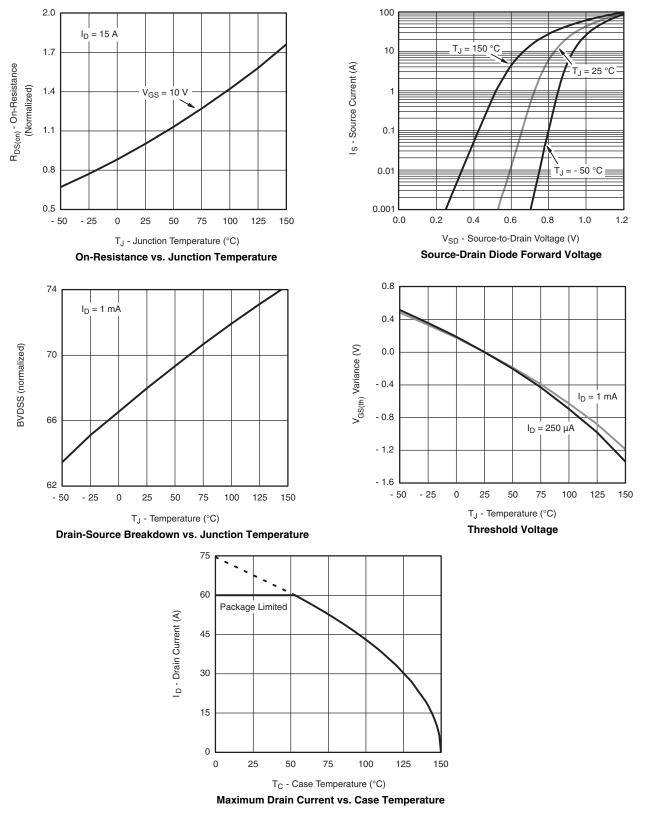


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

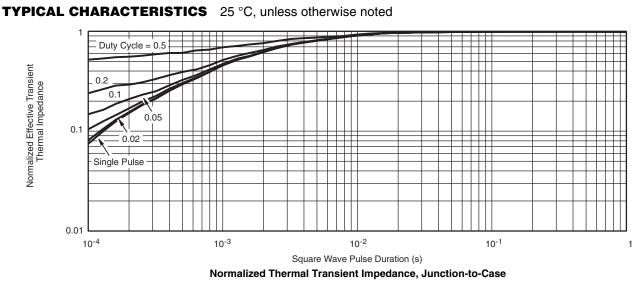






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Vishay Siliconix



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